

References

- [1] K. Zosel, and *Angew. Chem. Int. Ed. Engl*, vol. 17, pp. 702, 1978.
- [2] P. M. F. Paul, and W. S. Wise, *Mills&Boon, Ltd*, 1971.
- [3] J. F. Brennecke, and C. A. Eckert, *AIChEJ*, vol. 35, pp1049, 1989.
- [4] J. B. Rubin, L. B. Davenhall, C. M. V. Taylor, L. D. Sivils, T. Pierce, and K. Tiefert, *International LANL*, 1998.
- [5] L. B. Rothman, R. J. Robey, M. K. Ali, and D. J. Mount, *IEEE/SEMI Advanced Semiconductor manufacturing Conference*, 2002.
- [6] W. H. Mullee, M. A. Biberger, and P. E. Schilling, *United States Patent*, Patent 6500605 B1, 2002.
- [7] C. H. Lee, S. H. Hur, Y. C. Shin, J. H. Choi, D. G. Park, and K. Kim, *Appl. Phys. Lett.*, vol. 86, 152908, 2005.
- [8] G. D. Wilk, R. M. Wallace, and J. M. Anthony, *J. Appl. Phys.*, vol. 89, pp. 5243, 2001.
- [9] K. Nomura, H. Ohta, K. Ueda, T. Kamiya, M. Hirano, and H. Hosono, *SCIENCE*, 300, pp. 1269, 2003.
- [10] L. A. Majewski, R. Schroeder, M. Grell, P. A. Glarvey, and M. L. Turner, *J. Appl. Phys.*, 96, pp. 5781, 2004.
- [11] P. G. LeComber, W. E. Spear, and A. Ghaith, *IEEE Electron Device Lett.*, pp. 179, 1979.
- [12] M. Liu, Q. Fang, G. He, L. Q. Zhu, and L. D. Zhang, *J. Appl. Phys.*, vol. 101, 034107, 2007.
- [13] D. Brassard, D. K. Sarkar, M. A. El Khakani, and L. Ouellet, *J. Vac. Sci. Technol. A*, vol. 22(3), pp. 851, 2004.
- [14] Y. Ito, K. Suzulki, and R. Miura, *SISPAD 2006.*, pp. 150, 2006.
- [15] B. J. O'Sullivan, L. Pantisano, P. Roussel, R. Degraeve, G. Groeseneken, S.

- DeGendt, and M. M. Heyns, *J. Appl. Phys.*, vol. 101, 044515, 2007.
- [16] S. Jakschik, U. Schroeder, T. Hecht, M. Gutsche, H. Seidl, and J. W. Bartha, *Thin Solid Films*, vol. 425, pp. 216, 2003.
- [17] J. Lu, and Y. Kuo, *2004 4th IEEE Conf. Nanotech.*, pp. 398, 2004.
- [18] H. Y. Yu, N. Wu, M. F. Li, C. Zhu, B. J. Cho, D. L. Kwong, C. H. Tung, J. S. Pan, J. W. Chai, W. D. Wang, D. Z. Chi, C. H. Ang, J. Z. Zheng, and S. Ramanathan, *Appl. Phys. Lett.*, vol. 81, pp. 3618, 2002.
- [19] C. S. Yang, L. L. Smith, C. B. Arthur, and G. N. Parsons, *J. Vac. Sci. Technol. B*, vol. 18(2), pp. 683, 2000.
- [20] S. Ogawa, T. Nasuno, M. Egami, and A. Nakashima, *Interconnect Tech. Conf., Proc. of the IEEE 2002 International*, pp. 220, 2002.
- [21] P. T. Liu, C. T. Tsai, T. C. Chang, K. T. Kin, P. L. Chang, C. M. Chen, and H. F. Cheng, *Electrochem. Solid-State Lett.*, vol. 9(4), pp. G124, 2006.
- [22] P. T. Liu, C. T. Tsai, T. C. Chang, K. T. Kin, P. L. Chang, *IEEE Trans. Nanotech.*, vol. 6, pp. 29, 2007.
- [23] P.S. Bagus, F. Illas, G. Pacchioni, F. Parmigiani, *J. Electron Spectrosc. Related Phenom.* 100 (1999) 215.
- [24] H.Y. Yu, X.D. Feng, D. Grozea, Z.H. Lu, R.N.S. Sodhi, A.M. Hor, H. Aziz, *Appl. Phys. Lett.* 78 (2001) 2595.
- [25] J.P. Chang, Y.S. Lin, *J. Appl. Phys.* 90 (2001) 2964.
- [26] M. L. Lee and K. E. Markides, *Analytical Supercritical Fluid Chromatography and Extraction. Provo, UT: Chromatography Conferences*, 1990.
- [27] T. Tanaka, H. Asuma, K. Ogawa, Y. Shinagawa, K. Ono, and N. Konishi, *IEDM Tech. Dig.*, pp. 389, 1993.
- [28] Y. He, R. Hattori, and J. Kanicki, *IEEE Electron Device Lett.*, vol. 21(12), pp. 590, 2000.
- [29] H. C. Cheng, F. S. Wang, and C. Y. Huang, *IEEE Trans. Electron Devices*, vol. 44,

- pp. 64, 1997.
- [30] H. N. Chern, C. L. Lee, and T. F. Lei, *IEEE Trans. Electron Devices*, vol. 40, pp. 2301, 1993.
- [31] T. SAMESHIMA, M. SATOH, K. SAKAMOTO, A. HISAMATSU, K. OZAKI, and K. SAITOH, *Jpn. J. Appl. Phys.*, vol. 37, part 2, pp. L112, 1998.
- [32] M. KUNII, *Jpn. J. Appl. Phys.*, vol. 45, pp. 660-665, 2006.
- [33] K. KITAHARA, K. OHNISHI, Y. KATOH, R. YAMAZAKI, and T. KUROSAWA, *Jpn. J. Appl. Phys.*, vol. 42, part 1, pp. 6742, 2003.
- [34] T. SAMESHIMA, K. SAKAMOTO, Y. TSUNODA, and T. SAITOH, *Jpn. J. Appl. Phys.*, vol. 37, part. 2, pp. L1452, 1998.
- [35] W. J. Zhu, Tso-Ping Ma, Takashi Tamagawa, J. Kim, and Y. Di, *IEEE Electron Devices Lett.* vol. 23, No. 2, 2002.
- [36] Takeshi Yamaguchi, Hideki Satake, and Noburu Fukushima, *IEEE Trans. Electron Devices*, vol. 51, No. 5, 2004.
- [37] M. Houssa, M. Tuominen, et al., *J. Appl. Phys.*, vol. 87, No. 12, pp. 8615, 2000.
- [38] Sanghun Jeon, Hyundoek Yang, Dae-Gyu Park, and Hyunsang Hwang, *Jpn. J. Appl. Phys.*, vol. 31, pp. 2390-2393, 2002.
- [39] Dieter K. Schroder, Wiley-INTERSCIENCE, 1998.
- [40] M. Lenzlinger, and E. H. Snow, *J. Appl. Phys.*, vol. 40, pp. 278, 1969.
- [41] R. Mahapatra, A. K. Chakraborty, N. Poolamai, A. Horsfall, S. Chattopadhyay, and N. G. Wright, *J. Vac. Sci. Technol. B*, vol. 25(1), pp. 217, 2007.
- [42] P. R. Emtage, and W. Tantraporn, *Phys. Rev. Lett.*, vol. 8, pp. 267, 1962.
- [43] J. R. Yeagan, and H. L. Taylor, *J. Appl. Phys.*, vol. 39, pp. 5600, 1968.
- [44] T. FUKUDA, and H. YANAZAWA, *Jpn. J. Appl. Phys.*, vol. 43, pp. 936, 2004.
- [45] S. W. Huang, and J. G. Hwu, *IEEE Trans. Electron Devices*, vol. 50, pp. 1658, 2003.
- [46] F. Crupi, R. Degraeve, A. Kerber, D. H. Kwak, and G. Groeseneken, *IEEE 42nd*

Annual International Reliability Physics Symposium, pp. 181, 2004

[47] P. Servati, and A. Nathan, *J. Vac. Sci. Technol. A*, vol. 20(3), pp. 1038, 2002.

[48] M. POWELL, *IEEE Trans. Electron Devices*, vol. 36, pp. 2753, 1989.

[49] P. Servati, and A. Nathan, *IEEE Trans. Electron Devices*, vol. 49, pp. 812, 2002.

[50] T. Globus, H. C. slade, M. S. Shur, and M. Hack, *M.R.S. Proc.*, vol. 336, pp. 823, 1994.



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